PATENT COOPERATION TREATY

PCT

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

(Chapter II of the Patent Cooperation Treaty)

(PCT Article 36 and Rule 70)

Applicant's or agent's file reference 13225 Ko/tp	FOR FURTHER A	CTION	See Form PCT/IPEA/416						
International application No.	International filing dat	e (day/month/year)	Priority date (day/month/year)						
PCT/DE2004/001588	21.07.2004	4	23.07.2003						
International Patent Classification (IPC) or national classification and IPC									
H01L21/28, H01L21/336, H01L21/8246, H01L29/792, H01L27/115, H01									
L51/30									
Applicant INFINEON TECHNOLOGIES AG									
 This report is the international preliminary examination report, established by this International Preliminary Examining Authority under Article 35 and transmitted to the applicant according to Article 36. 									
2. This REPORT consists of a total of	7	sheets, including	g this cover sheet.						
3. This report is also accompanied by A									
a. (sent to the applicant and		many a total of 6	sheets, as follows:						
sheets of the description of the sheets containing relations.	sheets of the description, claims and/or drawings which have been amended and are the basis for this report and/or sheets containing rectifications authorized by this Authority (see Rule 70.16 and Section 607 of the Administrative Instructions).								
sheets which supersede earlier sheets, but which this Authority considers contain an amendment that goes beyond the disclosure in the international application as filed, as indicated in item 4 of Box No. I and the Supplemental Box.									
	1 D	(indicate time and numbe	or of electronic carrier(s))						
b. (sent to the International	Bureau only) a total of	(indicate type and numbe	er of electronic carrier(s))						
, containing a sequence listing and/or tables									
related thereto, in computer readable form only, as indicated in the Supplemental Box Relating to Sequence Listing (see Section 802 of the Administrative Instructions).									
4. This report contains indications rela	ting to the following iten	ns:							
Box No. I Basis of th	ne report								
Box No. II Priority									
Box No. III Non-estab	lishment of opinion with	regard to novelty, inven	tive step and industrial applicability						
Box No. IV Lack of un	nity of invention								
	No. 1 and 1								
Box No. VI Certain do	ocuments cited								
Box No. VII Certain defects in the international application									
Box No. VIII Certain observations on the international application									
Date of submission of the demand		Date of completion of the	his report						
Date of Submission of the demand									
Name and mailing address of the IPEA/EP		Authorized officer							
		T.Jankson No.							

Translation

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Box	No. I	Basis of the report							
1.	With indic	regard to the language, this report is based on the internation ated under this item.	nal application in the language in	which it was filed, unless otherwise					
		This report is based on translations from the original language which is the language of a translation furnished for the purp		, ·					
		international search (Rule 12.3 and 23.1(b))	international search (Rule 12.3 and 23.1(b))						
		publication of the international application (Rule 12.4))						
		international preliminary examination (Rule 55.2 and/	or 55.3)						
2.	recei		ard to the elements of the international application, this report is based on (replacement sheets which have been furnished to the Office in response to an invitation under Article 14 are referred to in this report as "originally filed" and are not annexed to 11):						
		the international application as originally filed/furnished	international application as originally filed/furnished						
	\bowtie	the description:							
		pages 1-20		as originally filed/furnished					
		pages*	received by this Authority on						
		pages*	received by this Authority on						
	\boxtimes	the claims:							
		nos.		as originally filed/furnished					
		nos.*	as amended (togethe	er with any statement) under Article 19					
		nos.* 1-22	received by this Authority on	13.05.2005 with letter of 13.05.2005					
		nos.*	received by this Authority on						
	\boxtimes	the drawings:							
		sheets 1/5-5/5		as originally filed/furnished					
		sheets*	received by this Authority on						
		sheets*	received by this Authority on						
		a sequence listing and/or any related table(s) – see Supplem	ental Box Relating to Sequence L	isting.					
3.		The amendments have resulted in the cancellation of:							
		the description, pages		·					
		the claims, nos.	the claims, nos.						
		the drawings, sheets/figs							
		the sequence listing (specify):	the sequence listing (specify):						
		any table(s) related to sequence listing (specify):							
4.		This report has been established as if (some of) the amend they have been considered to go beyond the disclosure as fi							
		the description, pages							
		the claims, nos.							
		the drawings, sheets/figs							
		the sequence listing (specify):							
		any table(s) related to sequence listing (specify):	<u>.</u> ,	-					
*	If ite	em 4 applies, some or all of those sheets may be marked "sup	erseded."						

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Box	No. V		atement under Article 35(2) with regard to novelty, inventive step or industrial applicability; I explanations supporting such statement		
1.	Statement				
	Novelty (N)	Claims 1-22	YES	
			Claims		
	Inventive	step (IS)	Claims	YES	
			Claims 1-22		
	Industrial	l applicability			
			Claims		
2.	Citation	d explanations			
<u> </u>		-			
	1. This report makes reference to the following documents:				
			JS-A-6 051 467 (CHA CHER LIANG ET AL) 18		
			April 2000 (2000-04-18)		
			JUNG DAL CHOI ET AL: "A triple polysilicon		
			stacked flash memory cell with wordline self-		
			boosting programming" ELECTRON DEVICES		
			MEETING, 1997. TECHNICAL DIGEST.,		
			INTERNATIONAL, WASHINGTON, DC, USA 7-10 DEC.		
			1997, NEW YORK, NY, USA, IEEE, US, 7 December		
			1997 (1997-12-07), pages 283-286, XP010265507		
			ISBN: 0-7803-4100-7		
			JS 2003/111670 A1 (KUHR WERNER G ET AL) 19		
			June 2003 (2003-06-19)		
		D4: U	JS 2002/015322 A1 (CLOUD EUGENE H ET AL) 7		
		E	February 2002 (2002-02-07)		
		D5: U	JS-A-5 981 335 (CHI MIN-HWA) 9 November 1999		
		•	(1999-11-09)		
	2.	The ar	oplication fails to meet the requirements of		
		PCT A	cticle 33(1) and (3) (inventive step).		
	2.1	D1 (se	ee column 1, line 57 to column 4, line 57;		

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Box No. V

steps:

paragraphs 1-11) is considered to be the closest prior art and discloses a method of producing a memory device having semiconductor structures and memory cells, said method having the following

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- a) production of a transistor having source/drain regions (26) and a gate dielectric (16) over the channel region;
- b) production of a first gate electrode (18) on the gate dielectric (16);
- c) completion "of processing of the semiconductor structures" from steps a) and b) by depositing and polishing an oxide layer (30);
- d) production of a storage layer (36) which is connected to the first gate electrode (18) by means of a conductive compound (32);
- e) production of an insulating layer (50, 54) over the storage layer (36).

Thus D1 and the subject matter of claims 1 and 11 differ in that, in the claims, a "second gate electrode" is provided over the storage layer, it being assumed that a gate electrode is characterized by the fact that it is connected in a non-conductive manner to the structure with respect to which it is intended to act as a gate (and the electrode 52 in D1 is therefore not regarded as such a gate electrode).

The objective technical problem to be solved is therefore that of making it possible to operate

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the memory device with the lowest possible voltages.

D2 discloses a method of improving a memory cell as known from D1 in such a way that the programming voltages are significantly reduced by using a "booster gate" electrode, which corresponds to the "second gate electrode" of the present application. This method is of interest to a person skilled in the art because the power consumption is thereby reduced. A person skilled in the art would therefore combine the teachings of D1 and D2 in order to provide an improved memory device.

The subject matter of independent claims 1 and 11 is therefore not inventive in relation to a combination of D1 and D2.

2.2 For the sake of completeness, the following should be noted.

An ONO layer per se (see layer 36 in D1) is generally known as a storage layer, i.e. electrical charges can be stored in an ONO layer. Whether, in a memory cell, the charge is in fact stored in the ONO layer or in another layer depends on the electrical voltages that are applied to or present at various points of the cell during use of the cell.

Claims 1 and 11 of the present application define

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- a layer structure and a method of producing the same, which method is also obvious from a combination of D1 and D2 (see point 2.1 above). The structure described in the claims does not, however, allow any conclusions to be made regarding the use thereof. For example, it is not clear from claims 1 and 11 whether or not the "first gate electrode" is/can be a floating gate (as known from D1); thus inter alia a floating gate falls under the scope of protection.
- 3. The remaining claims do not contain any features which, in combination with the features of any claim to which they refer, meet the requirements of PCT Article 33 for novelty and inventive step (see D1 to D5 and the corresponding passages in the search report).

Claims 2-3, 6, 12-13, 16 and 20 are disclosed in D1.

Claims 4-5, 7, 10, 14-15, 17 and 21-22: generally known features.

Claims 8-9 and 18-19: D3 discloses that storage layers are advantageously made of porphyrin molecules, and also discloses that, in the production process, all high-temperature steps must be carried out prior to deposition of the porphyrin molecules.

The application fails to meet the requirements of

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PCT Article 6 (clarity).

The description, page 5, lines 1-19, and page 6, lines 8-18, suggests that the following features are essential to the definition of the invention:

- (1) the storage layer is deposited only after completion of the process steps that require high temperatures;
- (2) the storage layer consists of an organic layer.

Since independent claims 1, 11 and 22 do not contain these features, these claims fail to meet the requirement of PCT Article 6 in conjunction with PCT Rule 6.3(b) that each independent claim must include all the technical features essential to the definition of the invention.

It should be noted that the feature of the storage layer being applied in a spatially separate manner with regard to the actual transistor region is not sufficient for describing the feature (1) above.